

2SC3931G

Silicon NPN epitaxial planar type

For high-frequency amplification

■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency f_T
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

■ Package

- Code
SMini3-F2
- Marking Symbol: U
- Pin Name
 1. Base
 2. Emitter
 3. Collector

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 30 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 20 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 3 | V |
| Collector current | I_C | 15 | mA |
| Collector power dissipation | P_C | 150 | mW |
| Junction temperature | T_j | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

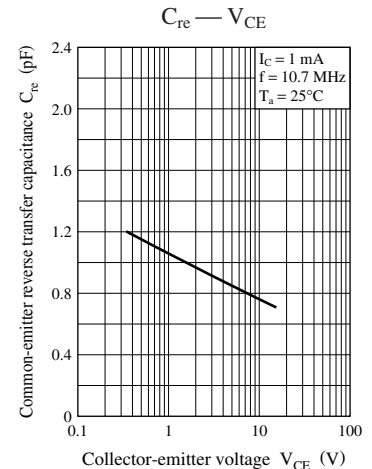
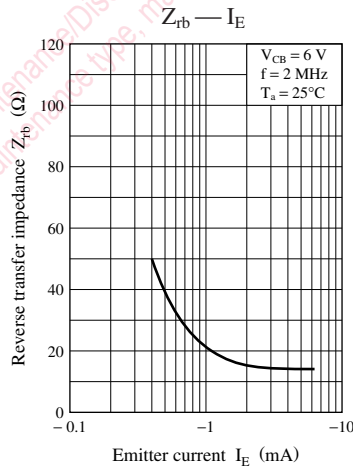
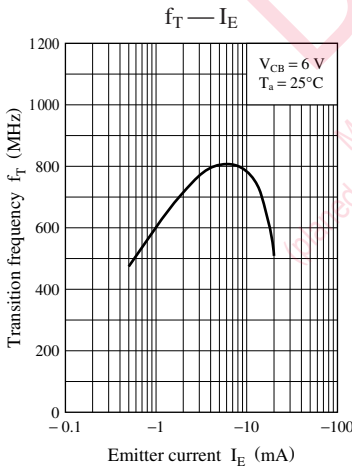
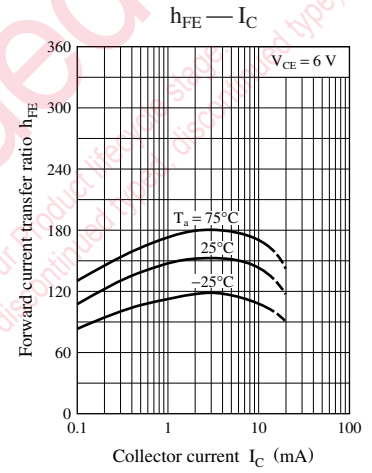
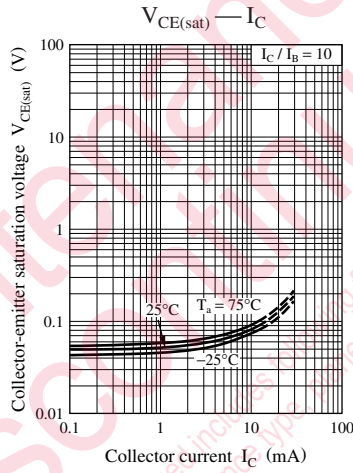
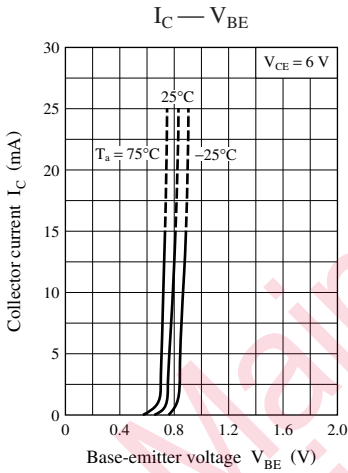
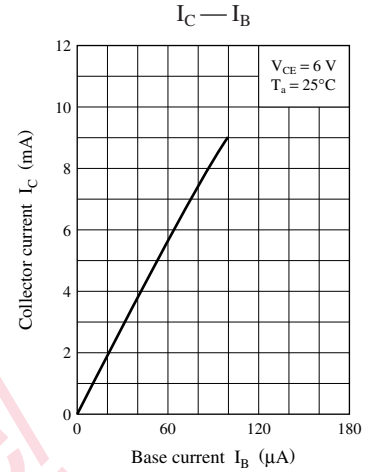
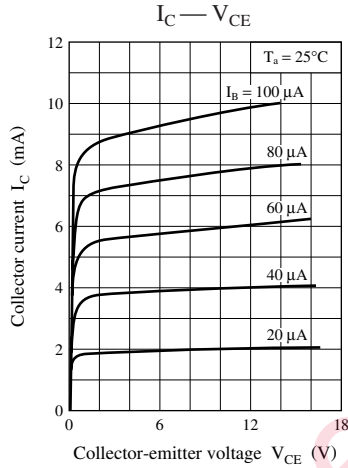
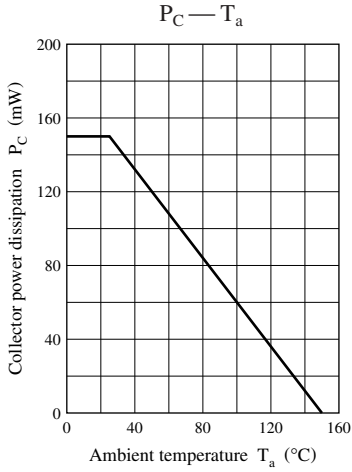
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

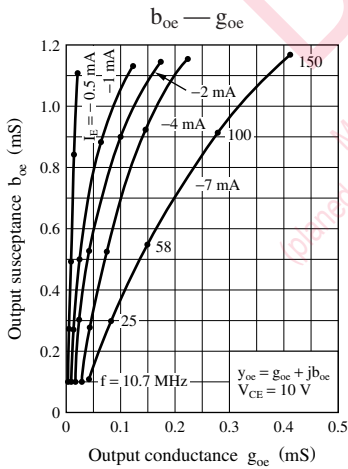
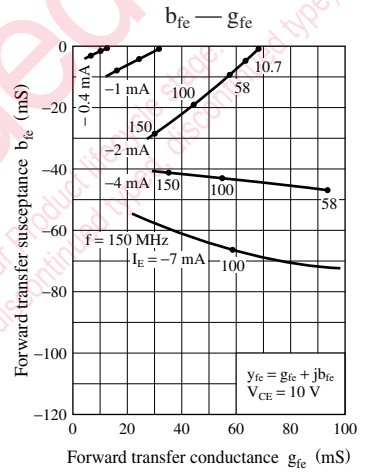
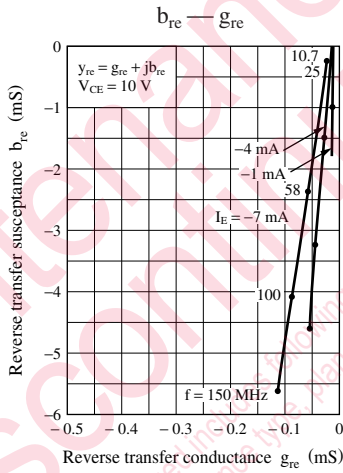
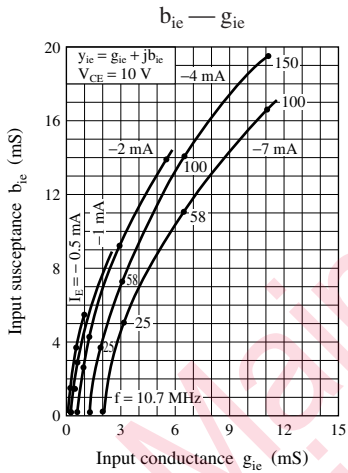
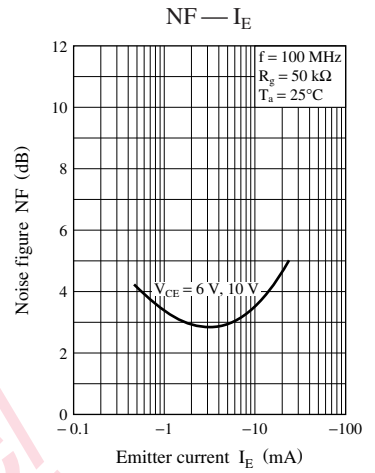
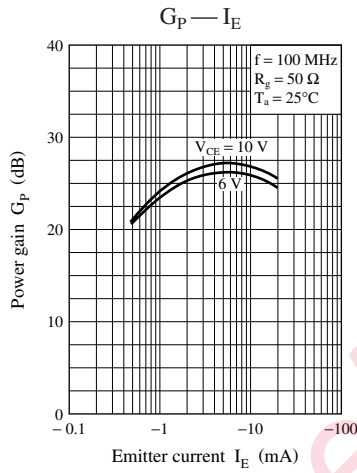
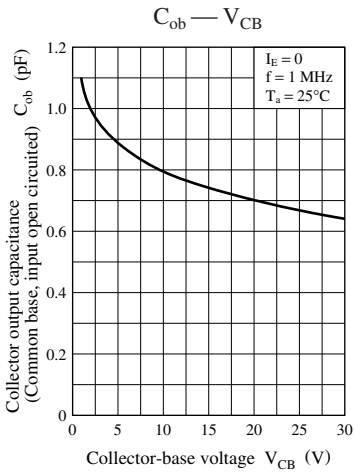
| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|---|-----------|---|-----|-----|-----|------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 30 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}, I_C = 0$ | 3 | | | V |
| Base-emitter voltage | V_{BE} | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$ | | 720 | | mV |
| Forward current transfer ratio * | h_{FE} | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$ | 65 | | 260 | — |
| Transition frequency | f_T | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 200 \text{ MHz}$ | 450 | 650 | | MHz |
| Common-emitter reverse transfer capacitance | C_{re} | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$ | | 0.8 | 1.0 | pF |
| Power gain | G_P | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$ | | 24 | | dB |
| Noise figure | NF | $V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$ | | 3.3 | | dB |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

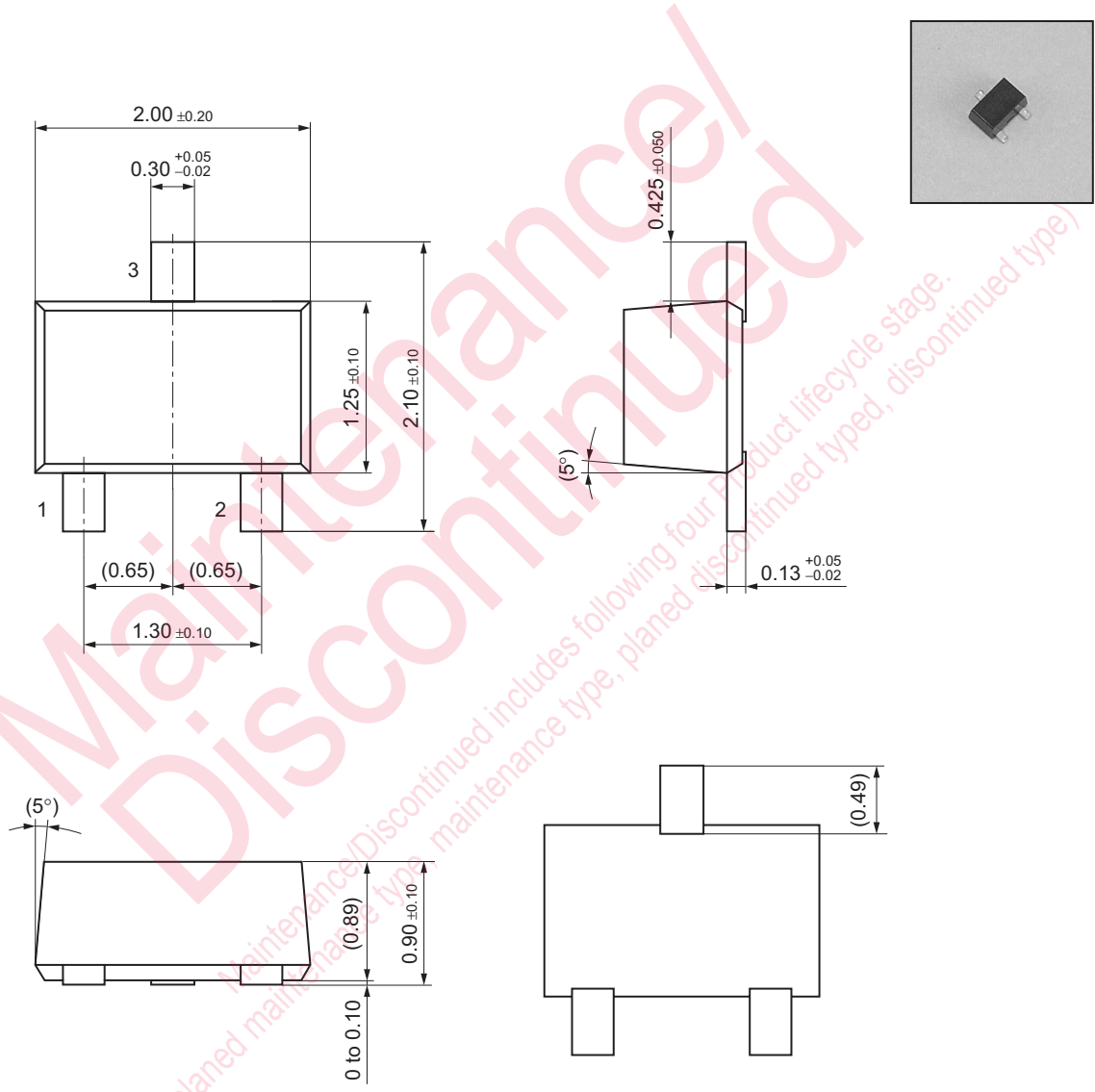
| Rank | C | D |
|----------|-----------|------------|
| h_{FE} | 65 to 160 | 100 to 260 |





SMini3-F2

Unit: mm



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